b) Amendments to the Claims

Kindly amend claim 7 as follows. A complete listing of all the claims that are or were in the application follows.

---

--1. (Withdrawn) A vacuum deposition system comprising a film-forming chamber to be kept at a stated degree of vacuum, and provided therein a substrate holder which holds a substrate and a vapor-generating means which generates a vapor of a deposition material which is to be vacuum-deposited on the surface of the substrate to come into a thin film, the system further comprising:

a reaction chamber provided therein with an ionization means which ionizes by the plasma a source gas for compensating atoms coming short in the thin film; and

a communicating portion which makes the inside of the film-forming chamber and the inside of the reaction chamber communicate with each other and has a pressure control means which controls differential pressure between the film-forming chamber and the reaction chamber.

2. (Withdrawn) The vacuum deposition system according to claim 1, which comprises a microwave-generating means for introducing microwaves into the reaction chamber.

3. (Withdrawn) The vacuum deposition system according to claim 1, which comprises a high-frequency power source for supplying a high-frequency power into the reaction chamber.

4. (Withdrawn) The vacuum deposition system according to claim 1, wherein the pressure control means is a pressure control valve.

5. (Withdrawn) The vacuum deposition system according to claim 1, which comprises a gas feed means for feeding the source gas into the reaction chamber.

6. (Withdrawn) The vacuum deposition system according to claim 5, wherein the gas feed means is a means for feeding into the reaction chamber at least one of oxygen gas and the fluorine gas as the source gas.

A1 cut

7. (Currently Amended) A thin-film deposition process which forms a thin film by means of ~~the~~ a vacuum deposition system comprising a film-forming chamber to be kept at a stated degree of vacuum, and provided therein a substrate holder which holds a substrate and a vapor-generating means which generates a vapor of a deposition material which is to be vacuum-deposited on the surface of the substrate to come into a thin film, the system further comprising

a reaction chamber provided therein with an ionization means which ionizes by the plasma a source gas for compensating atoms coming short in the thin film; and

a communicating portion which makes the inside of the film-forming chamber and the inside of the reaction chamber communicate with each other and has a pressure control means which controls differential pressure between the film-forming chamber and the reaction chamber ~~according to claim 1~~, the process comprising the steps of:

ionizing the source gas in the reaction chamber and thereafter opening the pressure control means of the communicating portion to introduce an ionized source gas into the film-forming chamber; and

generating a vapor of the deposition material in the film-forming chamber to form the thin film.

8. (Original) The thin-film deposition process according to claim 7, wherein the film-forming chamber is kept at an internal pressure of 13 mPa or less, and the reaction chamber is kept at an internal pressure of from 0.3 Pa to 7 Pa.--